IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: Not yet assigned   Examiner: Not yet assigned

Serial No. Not yet assigned   Filed: December 28, 2001

In re Application of: Hawley et al.

For: METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED
        TOTAL RADIATION-INDUCED LEAKAGE CURRENT

PRELIMINARY AMENDMENT

Director of Patents
Box New Application
Washington, D.C. 20231

Dear Sir:

Kindly amend the above-identified application as follows.

In the Specification:

Page 1, Line 8, please delete "MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT AND METHOD FOR FABRICATING SAME" and insert --METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT--.

Page 1, Line 11, please insert --This application is a divisional of United States Patent Application Serial Number 09/741,949, filed December 20, 2000, entitled "MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT AND METHOD FOR FABRICATING SAME".--

<u>In the Claims</u>

Kindly cancel claims 1-4 without traverse.

REMARKS

This application is a divisional including claims which were cancelled from the parent application in response to a Restriction Requirement.

In view of the foregoing, consideration and an early allowance of this application are earnestly solicited.

Respectfully submitted,
Sierra Patent Group, Ltd.

Dated: December 28, 2001

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